

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT1606N3T**

CHIP SIZE	0.36 * 0.36 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	119,000 pcs

Maximum Ratings (Ta=25°C)

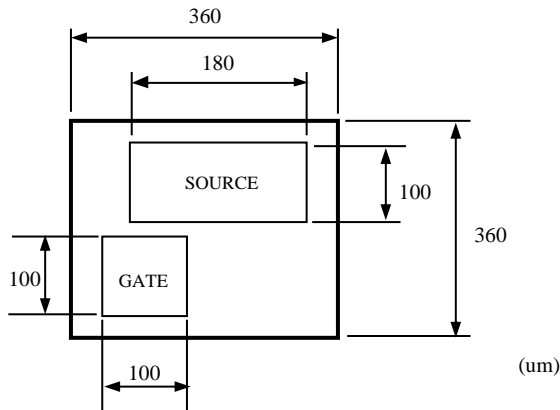
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	60	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	0.15	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±4	uA	VGS= ±20V VDS= 0V
2	IDSS			1	uA	VDS= 62V
3	BVDSS	62			V	ID= 100uA
4	VTH	1		2.0	V	ID= 250uA
5	RDS(on)1		3.5	5.5	Ω	VGS= 5.0V ID= 100mA
6	RDS(on)2		3	5	Ω	VGS= 10V ID= 100mA
7	Yfs	100			mS	VDS= 10V ID= 100mA

※ Built-in ZD between Gate and Source



NOTE: